

L Number	Hits	Search Text	DB	Time stamp
1	2820	438/627, 637, 643, 653.cccls. and @ad<20020102	USPAT; US-PPGPUB	2004/07/22 15:24
2	44	(438/627, 637, 643, 653.cccls. and @ad<20020102) and ((silicon adj carbide) with barrier)	USPAT; US-PPGPUB	2004/07/22 15:25
3	2409	438/672, 675, 700, 724, 761.cccls. and @ad<20020102	USPAT; US-PPGPUB	2004/07/22 15:29
4	20	(438/672, 675, 700, 724, 761.cccls. and @ad<20020102) and ((silicon adj carbide) with barrier)	USPAT; US-PPGPUB	2004/07/22 15:29
5	11	((438/672, 675, 700, 724, 761.cccls. and @ad<20020102) and ((silicon adj carbide) with barrier)) not ((438/627, 637, 643, 653.cccls. and @ad<20020102) and ((silicon adj carbide) with barrier))	USPAT; US-PPGPUB	2004/07/22 15:25
6	2346	438/634, 687, 688, 706.cccls. and @ad<20020102	USPAT; US-PPGPUB	2004/07/22 15:33
7	39	(438/634, 687, 688, 706.cccls. and @ad<20020102) and ((silicon adj carbide) with barrier)	USPAT; US-PPGPUB	2004/07/22 15:30
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DOCUMENT-IDENTIFIER: US 20030089992 A1

TITLE: SILICON CARBIDE DEPOSITION FOR USE
AS A BARRIER LAYER
AND AN ETCH STOP

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Abstract Paragraph - ABTX (1):

The present invention generally provides an improved process for depositing silicon carbide, using a silane-based material with certain process parameters, onto an electronic device, such as a semiconductor, that is useful for forming a suitable barrier layer, an etch stop, and a passivation layer for IC applications. As a barrier layer, in the preferred embodiment, the particular silicon carbide material is used to reduce the diffusion of copper and may also be used to minimize the contribution of the barrier layer to the capacitive coupling between interconnect lines. It may also be used as an etch stop, for instance, below an intermetal dielectric (IMD) and especially if the IMD is a low k, silane-based IMD. In another embodiment, it may be used to provide a passivation layer, resistant to moisture and other adverse ambient conditions. Each of these aspects may be used in a dual damascene structure.

Application Filing Date - APD (1):

19981001

Current US Classification, US Secondary Class/Subclass -
CCSR (9) :

438/634

Current US Classification, US Secondary Class/Subclass -

CCSR (10) :

438/687

Title - TTL (1) :

SILICON CARBIDE DEPOSITION FOR USE AS A BARRIER LAYER
AND AN ETCH STOP

Summary of Invention Paragraph - BSTX (2) :

[0001] The present invention relates generally to the fabrication of integrated circuits on substrates. More particularly, the invention relates to a low temperature method for producing a silicon carbide film utilizing alkyl silanes under certain process regimes, which may be useful as a barrier layer, etch stop, and passivation layer.

Summary of Invention Paragraph - BSTX (10) :

[0008] Therefore, there is a need for an improved process using silicon carbide as a barrier layer, an etch stop, and a passivation layer for ICs.

Summary of Invention Paragraph - BSTX (12) :

[0009] The present invention generally provides an improved process for depositing silicon carbide, using a silane-based material with certain process parameters, onto an electronic device, such as a semiconductor, that is useful for forming a suitable barrier layer, an etch stop, and a passivation layer for IC applications. As a barrier layer, in the preferred embodiment, the particular silicon carbide material is used to reduce the diffusion of copper and may also be used to minimize the contribution of the barrier layer to the capacitive coupling between interconnect lines. It may also be used as an etch stop, for instance, below an intermetal dielectric (IMD) and especially if the

IMD is a low k, silane-based IMD. In another embodiment, it may be used to provide a passivation layer, resistant to moisture and other adverse ambient conditions. Each of these aspects may be used in a dual damascene structure.

Summary of Invention Paragraph - BSTX (13) :

[0010] A preferred process sequence for forming a silicon carbide barrier layer on a substrate, comprises introducing silicon, carbon, and a noble gas into a reaction zone of a process chamber, initiating a plasma in the reaction zone, reacting the silicon and the carbon in the presence of the plasma to form silicon carbide, and depositing a silicon carbide barrier layer on a substrate in the chamber. Another sequence comprises introducing silicon, carbon, and a noble gas in a reaction zone of a chamber, initiating a plasma in the reaction zone, reacting the silicon and the carbon in the presence of the plasma to form silicon carbide, and depositing a silicon carbide passivation layer on the substrate. Still another aspect may include a substrate having a silicon carbide barrier layer, comprising a semiconductor substrate, a dielectric layer deposited on the substrate, and a silicon carbide barrier layer having a dielectric constant of about 6 or less.

Detail Description Paragraph - DETX (18) :

[0032] In addition to serving as an improved barrier/etch stop layer, the SiC films of the present invention may also be used as a passivation layer. The passivation layer may play an increasingly larger role in copper-based devices, because the copper diffuses into surrounding layers. Furthermore, the silicon carbide material, with some process modifications compared to the most preferred parameters of the barrier/etch stop material,